



**INFORMATION DISCLOSURE
CITATION**

ATTY. DOCKET NO.

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IMAI ET AL.

(Use several sheets if necessary)

FILING DATE

GROUP


August 15, 2006

2812

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

							TRANSLATION	
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
/PD/	3-6826 A	1-1991	JP			Partial		
	52-78374	1-1977	JP			Partial		
	2002-57154 A	2-2002	JP			Partial		
/PD/	2002-64093 A	2-2002	JP			Partial		

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

/PD/	Sakamoto et al, "Formation of Anodic Reaction Film on n-type Si", Applied Physics, vol. 44, Issue No. 5, 1975, pp.497-506
↓	Tokuyama, "Comprehensive Treatise on Electronics Technology", Vol. 3, MOS Device, Kogyochosakai, 1976, pp.124-126
↓	Asusha et al, "Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density Formed by Chemical Oxidation of Si", Applied Physics Letters, Vol. 81, No. 18, 28 October 2002, pp. 3410-3412
↓	Kobayashi et al, "Nitric Acid Oxidation of Si to Form Ultrathin Silicon Dioxide Layers with a Low Leakage Current Density", Journal of Applied Physics, Vol. 94, No. 11, American Institute of Physics, 2003, pp. 7328-7335
/PD/	Asuha et al, "Low Temperature Formation of SiO ₂ /Si Structure by Chemical Method and Spectroscopic Observation", Meeting Abstracts of the Physical Society of Japan, Vol. 58, Issue 2, Part 4, Meeting Abstracts, 2003, pp. 771-

Examiner

/Phuc Dang/

Date Considered

04/02/2008

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)